

CMPDM7120G

**SURFACE MOUNT
N-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET**



SOT-23 CASE

- Device is **Halogen Free** by design

APPLICATIONS:

- Load/Power switches
- Power supply converter circuits
- Battery powered portable equipment

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

Drain-Source Voltage	
Gate-Source Voltage	
Continuous Drain Current (Steady State)	
Maximum Pulsed Drain Current, $t_p=10\mu\text{s}$	
Power Dissipation	
Operating and Storage Junction Temperature	
Thermal Resistance	



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPDM7120G is an Enhancement-mode N-Channel Field Effect Transistor, manufactured by the N-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications. This MOSFET offers low $r_{DS(ON)}$ and low threshold voltage.

MARKING CODE: C71G

FEATURES:

- ESD protection up to 2kV
- Low $r_{DS(ON)}$ (0.25Ω MAX @ $V_{GS}=1.5\text{V}$)
- High current ($I_D=1.0\text{A}$)
- Logic level compatibility
- Small SOT-23 package

SYMBOL		UNITS
V_{DS}	20	V
V_{GS}	8.0	V
I_D	1.0	A
I_{DM}	4.0	A
P_D	350	mW
T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Θ_{JA}	357	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

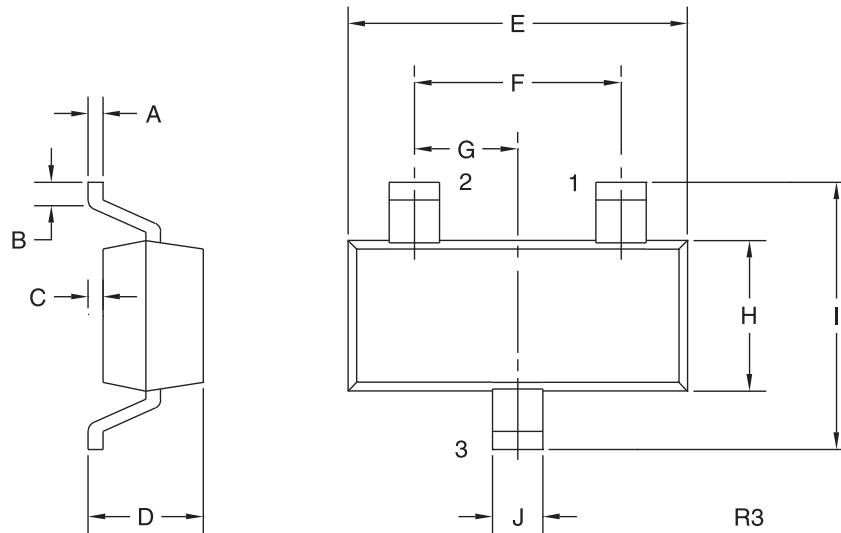
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSS}, I_{GSSR}	$V_{GS}=8.0\text{V}, V_{DS}=0$			10	μA
I_{DSS}	$V_{DS}=20\text{V}, V_{GS}=0$			10	μA
BV_{DSS}	$V_{GS}=0, I_D=250\mu\text{A}$	20			V
$V_{GS(th)}$	$V_{DS}=10\text{V}, I_D=1.0\text{mA}$	0.5		1.2	V
V_{SD}	$V_{GS}=0, I_S=1.0\text{A}$			1.1	V
$r_{DS(ON)}$	$V_{GS}=4.5\text{V}, I_D=0.5\text{A}$		0.075	0.10	Ω
$r_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=0.5\text{A}$		0.10	0.14	Ω
$r_{DS(ON)}$	$V_{GS}=1.5\text{V}, I_D=0.1\text{A}$		0.17	0.25	Ω
g_{FS}	$V_{DS}=10\text{V}, I_D=0.5\text{A}$		4.2		S
C_{rss}	$V_{DS}=10\text{V}, V_{GS}=0, f=1.0\text{MHz}$		45		pF
C_{iss}	$V_{DS}=10\text{V}, V_{GS}=0, f=1.0\text{MHz}$		220		pF
C_{oss}	$V_{DS}=10\text{V}, V_{GS}=0, f=1.0\text{MHz}$		120		pF
t_{on}	$V_{DD}=10\text{V}, V_{GS}=5.0\text{V}, I_D=0.5\text{A}$		25		ns
t_{off}	$V_{DD}=10\text{V}, V_{GS}=5.0\text{V}, I_D=0.5\text{A}$		140		ns

R1 (27-January 2010)

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SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Gate
- 2) Source
- 3) Drain

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DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

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